

AMENDMENTS TO THE CLAIMS, COMPLETE LISTING OF CLAIMS
IN ASCENDING ORDER WITH STATUS INDICATOR

Please amend the following claims as indicated.

1. (Currently Amended) A method for manufacturing an SOI wafer comprising the steps of:

inspecting a wafer on the presence or absence of a pit cluster which is a collection where tens or more of micro-defects each in the shape of a pit having a size of the order of 0.08 to 0.2 μm collect, and a size thereof of 1 μm to 10 μm ,

preparing two starting wafers on each of which no said pit cluster is present,
forming an insulating layer on at least one wafer of the two starting wafers; and
adhering the one wafer to the other wafer without using an adhesive,
wherein a PV value of a surface of the insulating layer is 1.5 nm or less.

2. (Canceled).

3. (Currently Amended) The method for manufacturing an SOI wafer according to claim 1, comprising the steps of:

inspecting two starting wafers on the presence or absence of a pit cluster which is a collection where tens or more of micro-defects each in the shape of a pit having a size of the order of 0.08 to 0.2 μm collect, and a size thereof is 1 μm to 10 μm ,

preparing two starting wafers on each of which no said pit cluster is present,
forming an insulating layer on at least one wafer of the two starting wafers;
implanting hydrogen ions or rare gas ions through an upper surface of the one wafer to form a micro-bubble layer in the interior of the one wafer; thereafter

bringing the surface of the one wafer through which the ions have been implanted into contact with the other wafer through the insulating layer interposed therebetween; then

separating a part of the one wafer with the micro-bubble layer as a cleavage plane by applying heat treatment for the rest thereof to become a thin film; and

bonding strongly the one wafer in the form of a thin film to the other wafer through the insulating layer interposed therebetween by applying further heat treatment.

Claims 4-8 (Canceled).

9. (Currently Amended) The method for manufacturing an SOI wafer according to claim 1, wherein wafers mirror polished and stored after the polishing in an environment where a heavy metal concentration is 10 ppb or less are used as the starting wafers.

10. (Canceled)

11. (Currently Amended) The method for manufacturing an SOI wafer according to claim 3, wherein wafers mirror polished and stored after the polishing in an environment where a heavy metal concentration is 10 ppb or less are used as the starting wafers.

Claims 12-16 (Canceled).